

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

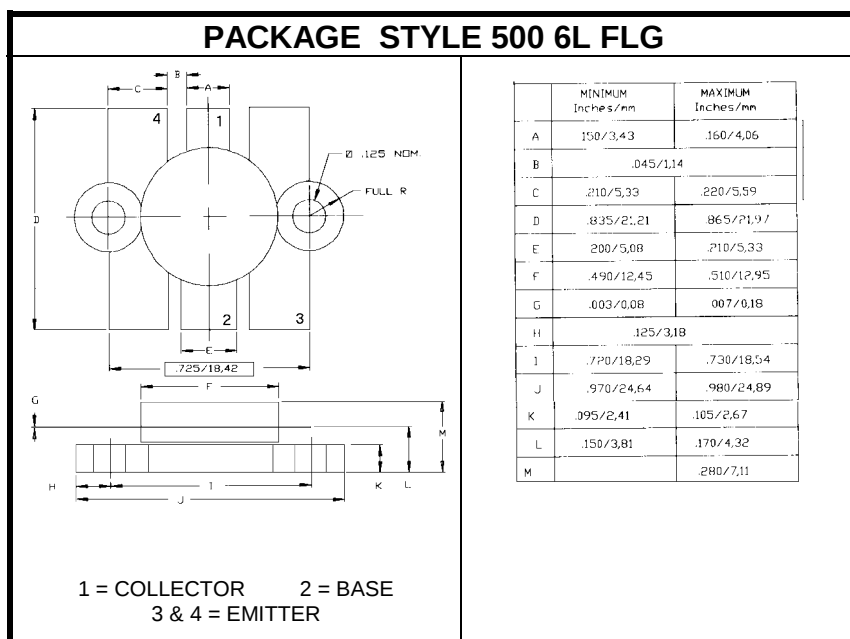
The **ASI TPV385** is Designed for Operation in Band III TV Transposers and Transmitter Amplifiers from 170 to 230 MHz.

FEATURES INCLUDE:

- Gold Metalization
- Emitter Ballast Resistors
- Internal Input Matching
- Common Emitter

MAXIMUM RATINGS

I_C	10 A (CONT)
V_{CB}	65 V
V_{CE}	35 V
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +200 °C
θ_{JC}	1.5 °C/W



CHARACTERISTICS $T_C = 25\text{ }^{\circ}\text{C}$

SYMBOL	TEST CONDITIONS		MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	$I_C = 50\text{ mA}$		35			V
BV_{CER}	$I_C = 50\text{ mA}$	$R_{BE} = 10\text{ }\Omega$	60			V
BV_{CBO}	$I_C = 50\text{ mA}$		65			V
BV_{EBO}	$I_E = 10\text{ mA}$		4.0			V
h_{FE}	$V_{CE} = 5.0\text{ V}$	$I_C = 1.0\text{ A}$	20		100	---
C_{ob}	$V_{CB} = 30\text{ V}$	$f = 1.0\text{ MHz}$		65	85	pF
G_p IMD_1	$V_{CE} = 28\text{ V}$	$P_{out} = 14\text{ W}$	14	15	-53	dB dB
ψ	$V_{CE} = 28\text{ V}$ $P_{out} = 14\text{ W}$	ALL PHASE ANGLES LOAD $VSWR = \infty:1$	$f = 225\text{ MHz}$ NO DEGRADATION IN OUTPUT POWER			